

Fig. 4-18 SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 8W. The scan speed are (a) 10cm/sec and (b) 7cm/sec

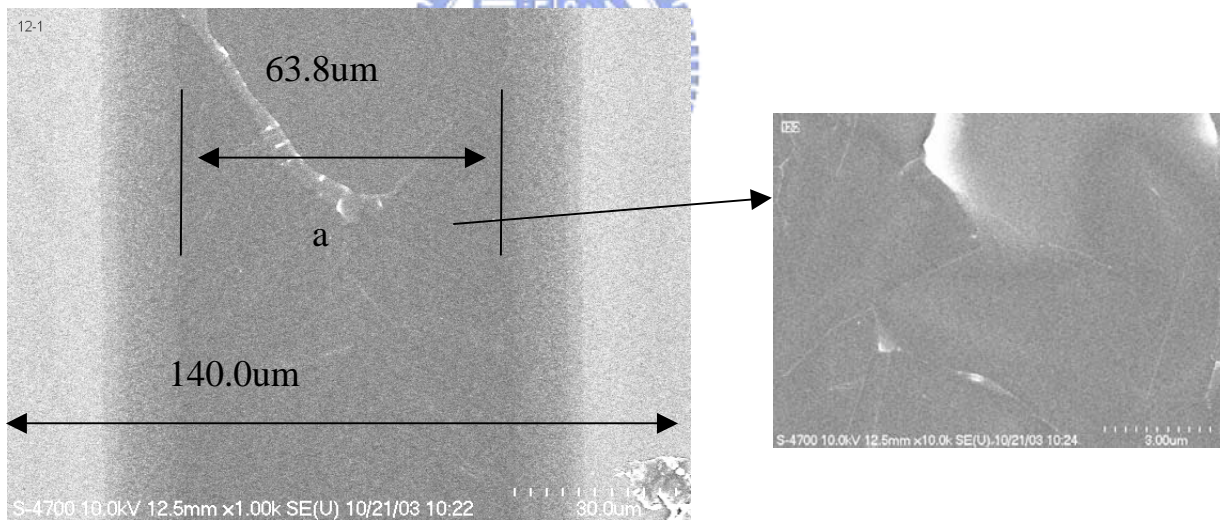


Fig. 4-19 SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 8W. The scan speed is 12 cm/sec, the grain size of area “a” is larger than 3μm

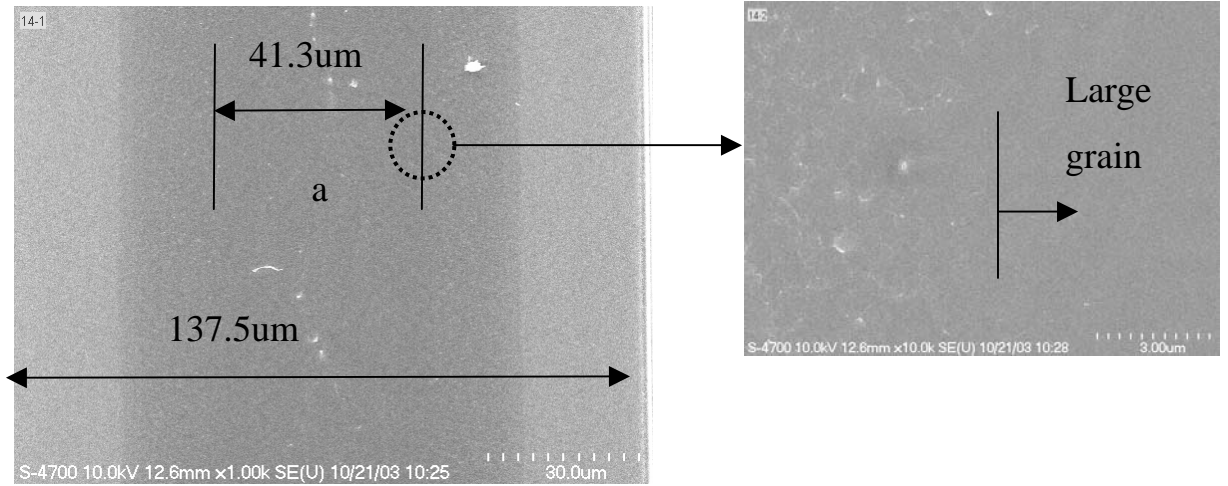


Fig. 4-20 SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 8W. The scan speed is 14 cm/sec, the grain size of center area is larger than 3um

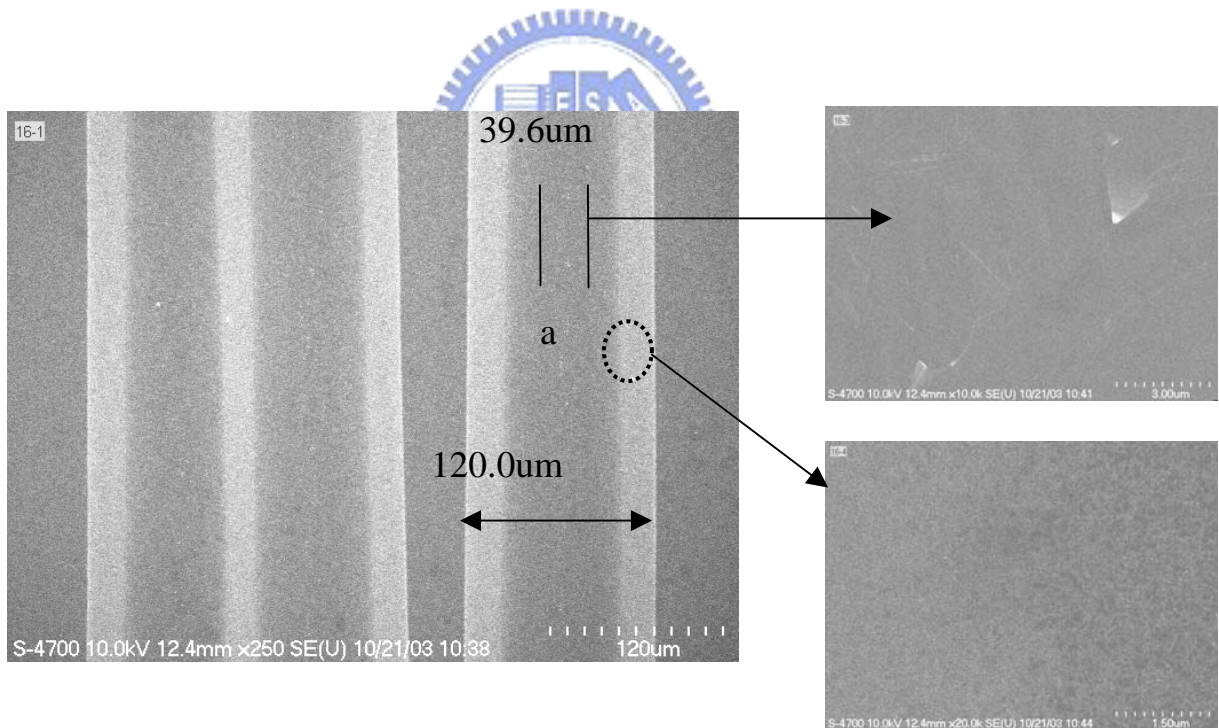


Fig. 4-21 SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 8W. The scan speed is 16 cm/sec, the grain size of area "a" is larger than 3um

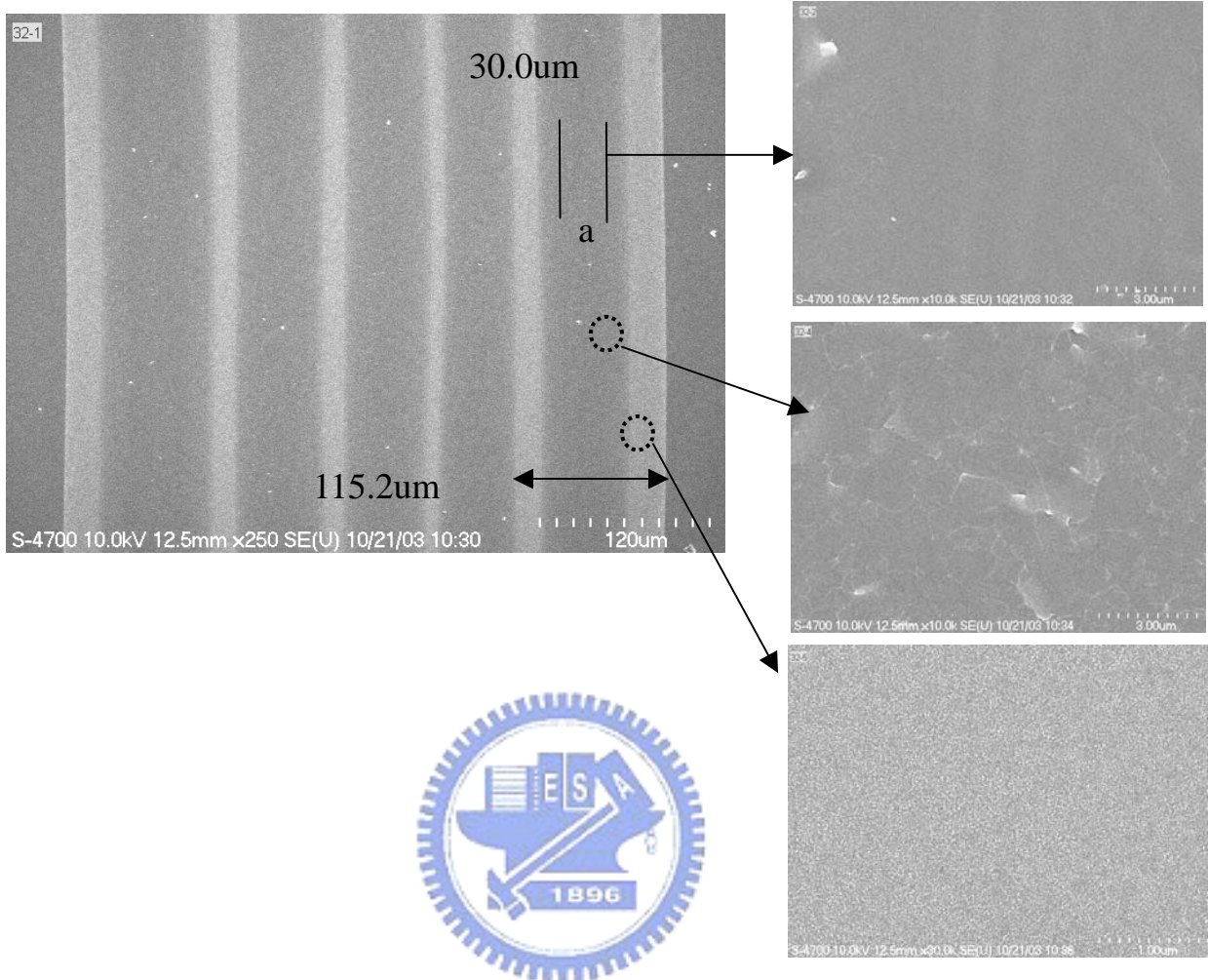


Fig. 4-22 SEM micrographs of CW laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The constant laser power is 8W. The scan speed is 32 cm/sec, the grain size of area “a” is larger than 3um